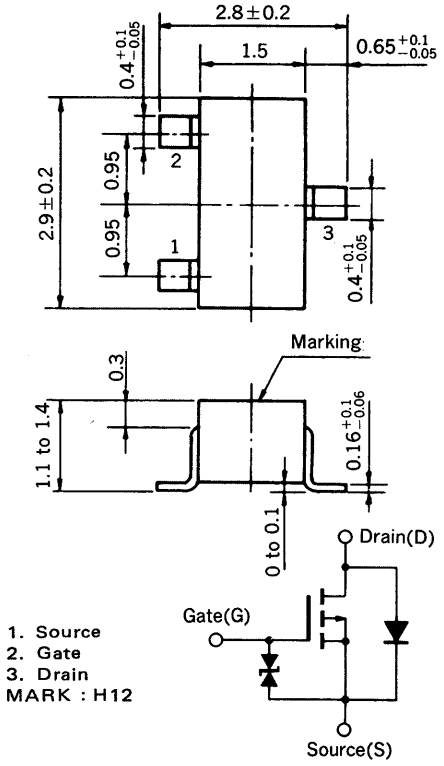
MOS FIELD EFFECT TRANSISTOR
2SJ185

P-CHANNEL MOS FET
FOR HIGH-SPEED SWITCHING

OUTLINE DIMENSIONS (Unit : mm)



1. Source
2. Gate
3. Drain

MARK : H12

(Diode in the figure is the parasitic diode.)

The 2SJ185 is a P-channel vertical type MOS FET which can be driven by 2.5 V power supply.

As the MOS FET is driven by low voltage and does not require consideration of driving current, it is suitable for appliances including VTR cameras and headphone stereos which need power saving.

FEATURES

- Directly driven by ICs having a 3 V power supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.
- Complementary to 2SK1399

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	RATINGS	UNIT	TEST CONDITIONS
Drain to Source Voltage	V_{DSS}	−50	V	V_{GS} = 0
Gate to Source Voltage	V_{GSS}	∓7.0	V	V_{DS} = 0
Drain Current	$I_{D(DC)}$	∓100	mA	
Drain Current	$I_{D(pulse)}$	∓200	mA	PW ≤ 10 ms, Duty Cycle ≤ 50 %
Total Power Dissipation	P_T	200	mW	
Operating Temperature	T_{opt}	−55 to +80	°C	
Storage Temperature	T_{stg}	−55 to +150	°C	

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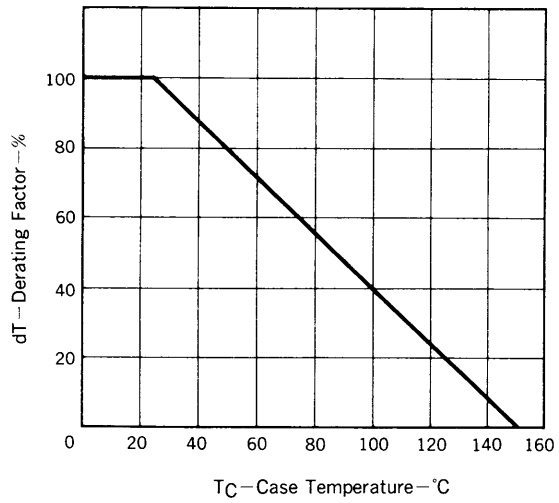
ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

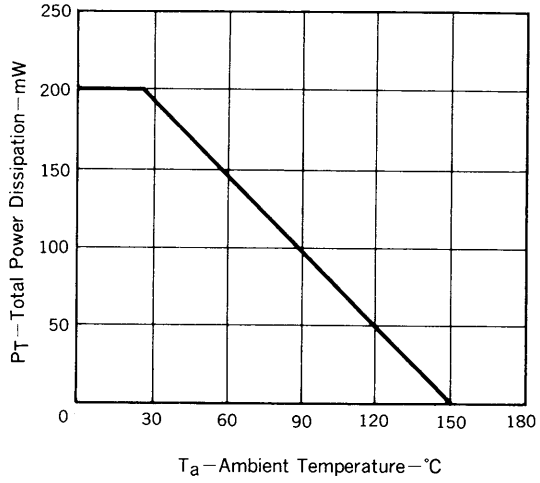
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Drain Cut-off Current	I_{DSS}			−10	μA	V_{DS} = −50 V, V_{GS} = 0
Gate Leakage Current	I_{GSS}			∓5	μA	V_{GS} = ∓7.0 V, V_{DS} = 0
Gate Cut-off Voltage	$V_{GS(off)}$	−1.2	−1.6	−2.0	V	V_{DS} = −3 V, I_D = −1 μA
Forward Transfer Admittance	$\|y_{fs}\|$	20	42		mS	V_{DS} = −3 V, I_D = −10 mA
Drain to Source On-State Resistance	$R_{DS(on)1}$		25	40	Ω	V_{GS} = −2.5 V, I_D = −1 mA
Drain to Source On-State Resistance	$R_{DS(on)2}$		13	20	Ω	V_{GS} = −4.0 V, I_D = −10 mA
Input Capacitance	C_{iss}		22		pF	V_{DS} = −3 V, V_{GS} = 0, f = 1 MHz
Output Capacitance	C_{oss}		12		pF	
Feedback Capacitance	C_{rss}		4		pF	
Turn-On Delay Time	$t_{d(on)}$		80		ns	$V_{GS(on)}$ = −3 V, R_G = 10 Ω, V_{DD} = −3 V, I_D = −20 mA, R_L = 150 Ω
Rise Time	t_r		230		ns	
Turn-Off Delay Time	$t_{d(off)}$		40		ns	
Fall Time	t_f		70		ns	

TYPICAL CHARACTERISTICS (T_a = 25 °C)

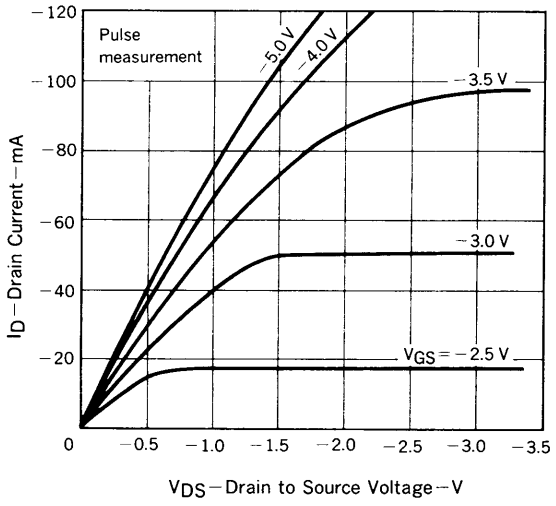
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



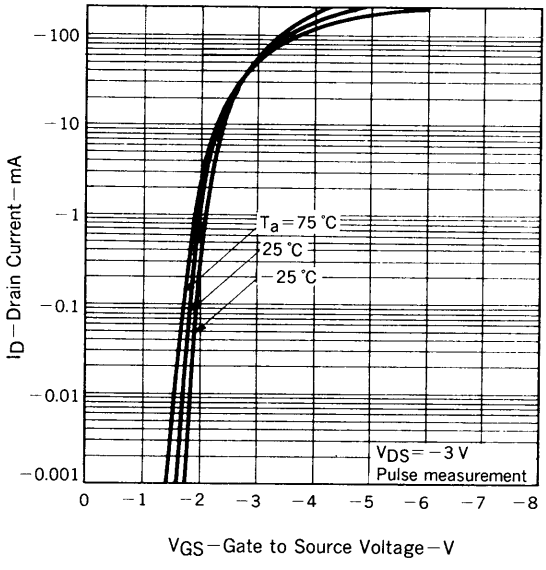
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



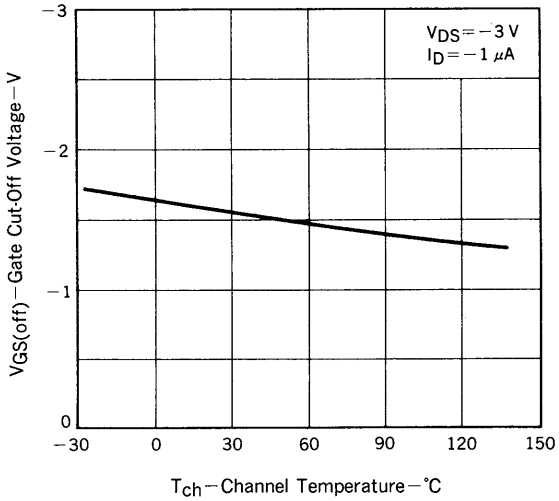
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



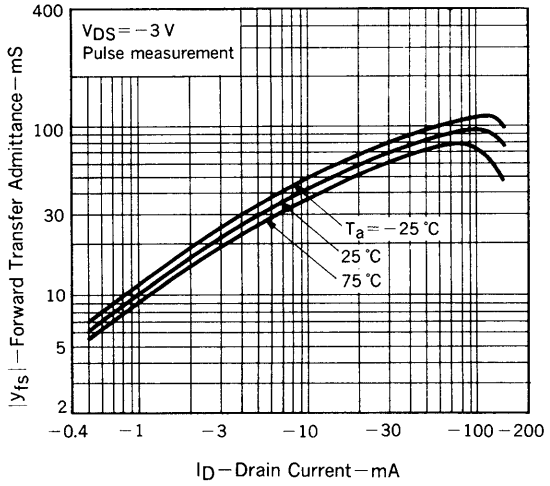
TRANSFER CHARACTERISTICS



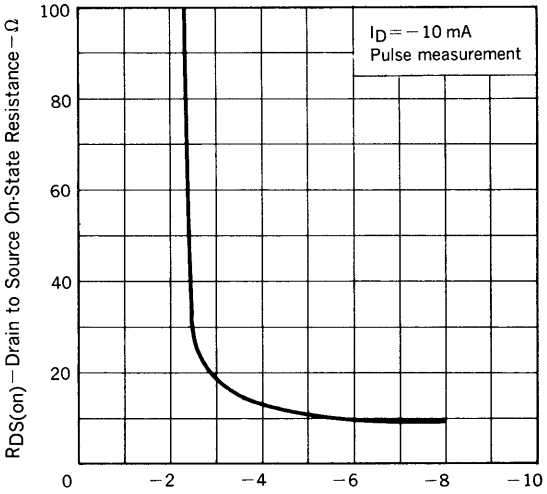
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



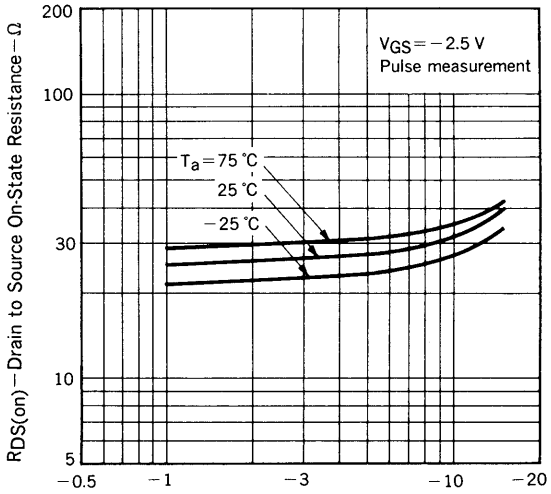
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



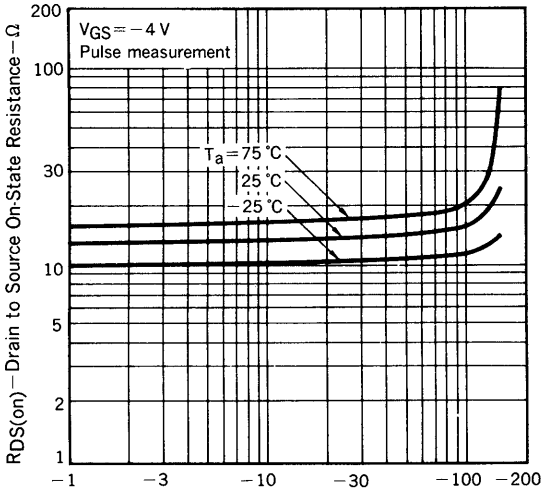
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



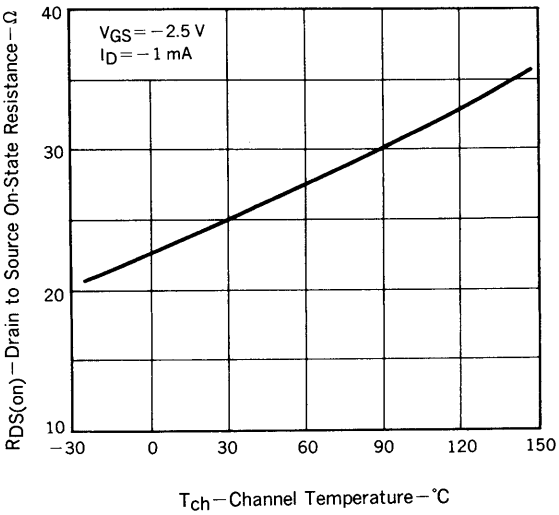
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



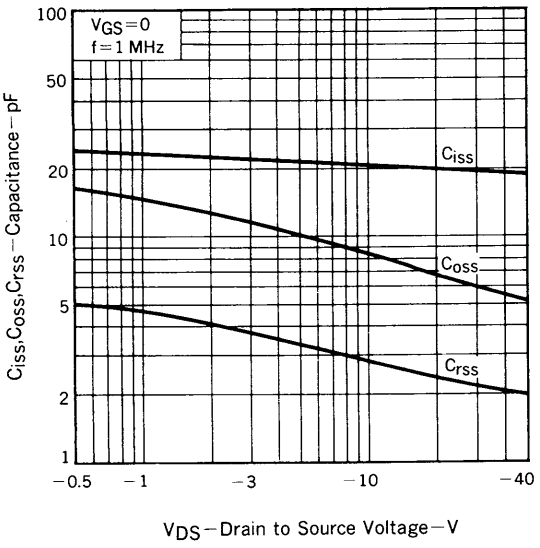
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



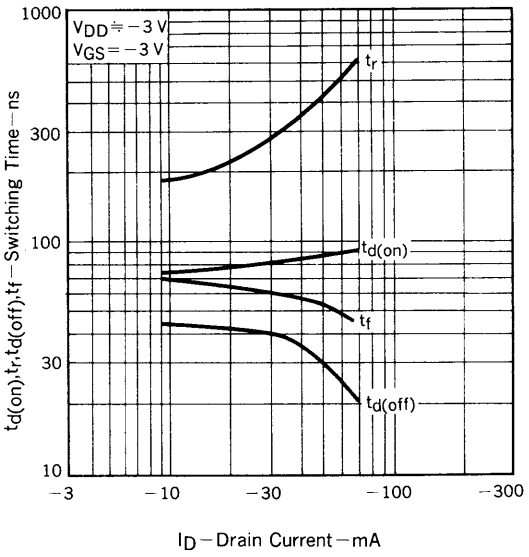
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



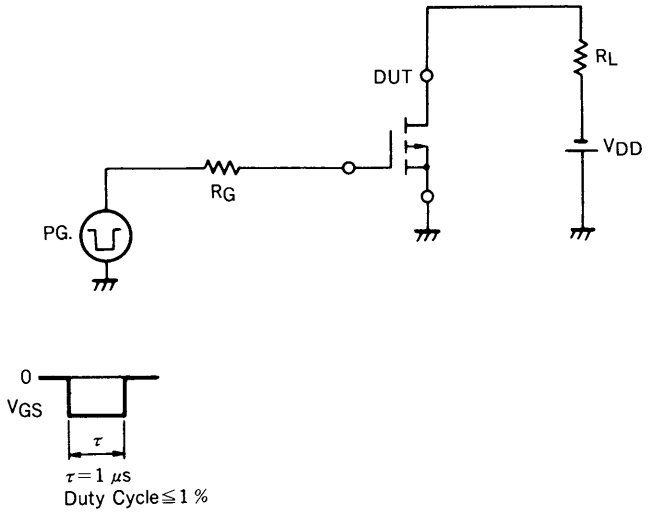
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

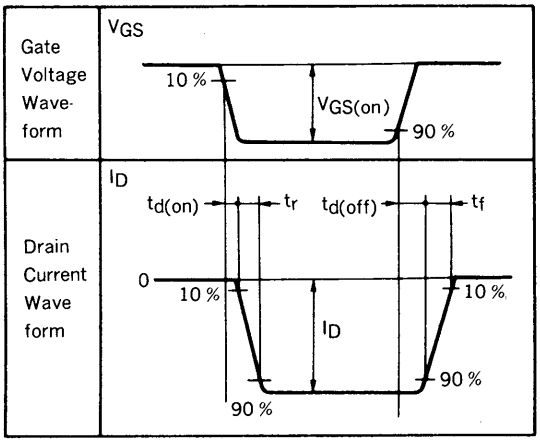


SWITCHING CHARACTERISTICS



SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS





RECOMMENDED SOLDERING CONDITIONS

Mounting of this product by soldering should be done under the following conditions.
Please consult our representatives about soldering methods and conditions other than these.

SURFACE MOUNT TYPE

For details of the recommended soldering conditions, see the information document.
"Device Mounting Manual for Surface Mounting (IEI-616)."

Soldering Method	Soldering Conditions	Symbol for Recommended Conditions
Infrared Reflow	Package peak temp.: 210 °C Soldering time: within 30 sec (above 210 °C) Soldering times: 1, Days limitation: none*	IR30-00
Vapor Phase Soldering	Package peak temp.: 215 °C Soldering time: within 40 sec (above 200 °C) Soldering times: 1, Days limitation: none*	VP15-00
Wave Soldering	Soldering bath temp.: below 260 °C Soldering time: within 10 sec Soldering times: 1, Days limitation: none*	WS60-00

*: Stored days under storage conditions at 25 °C and below 65 % R.H. after the dry-pack has been opened.

Note 1 Combination of soldering methods should be avoided.

[MEMO]